BD675, BD675A, BD677, BD677A, BD679, BD679A, BD681

Plastic Medium-Power Silicon NPN Darlingtons

This series of plastic, medium-power silicon NPN Darlington transistors can be used as output devices in complementary general-purpose amplifier applications.

Features

- High DC Current Gain
- Monolithic Construction
- Complementary to BD676, 676A, 678, 678A, 680, 680A, 682
- BD677, 677A, 679, 679A are Equivalent to MJE 800, 801, 802, 803
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	BD675, A BD677, A BD679, A BD681	V _{CEO}	45 60 80 100	Vdc
Collector-Base Voltage	BD675, A BD677, A BD679, A BD681	V _{CBO}	45 60 80 100	Vdc
Emitter-Base Voltage		V _{EBO}	5.0	Vdc
Collector Current		I _C	4.0	Adc
Base Current		Ι _Β	1.0	Adc
Total Device Dissipation @ Derate above 25°C	T _C = 25°C	P _D	40 0.32	W W/°C
Operating and Storage Jur Temperature Range	nction	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

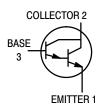
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θЈС	3.13	°C/W



ON Semiconductor®

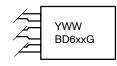
http://onsemi.com

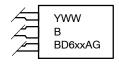
4.0 AMPERES POWER TRANSISTORS NPN SILICON 60, 80, 100 VOLTS, 40 WATTS





MARKING DIAGRAMS





BD6xx = Device Code

x = 75, 77, 79, 81

Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BD675, BD675A, BD677, BD677A, BD679, BD679A, BD681

ELECTRICAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage, (Note 1) $(I_C = 50 \text{ mAdc}, I_B = 0)$	BD675, 675A BD677, 677A BD679, 679A BD681	BV _{CEO}	45 60 80 100	- - - -	Vdc
Collector Cutoff Current (V _{CE} = Half Rated V _{CEO} , I _B = 0)		I _{CEO}	-	500	μAdc
Collector Cutoff Current $(V_{CB} = Rated\ BV_{CEO},\ I_E = 0)$ $(V_{CB} = Rated\ BV_{CEO},\ I_E = 0,\ T_C = 100'C)$		I _{CBO}	- -	0.2 2.0	mAdo
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		I _{EBO}	_	2.0	mAdd
ON CHARACTERISTICS					
DC Currert Gain, (Note 1) $ (I_C = 1.5 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}) $ $ (I_C = 2.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}) $	BD675, 677, 679, 681 BD675A, 677A, 679A	h _{FE}	750 750	- -	-
Collector–Emitter Saturation Voltage, (Note 1) ($I_C = 1.5$ Adc, $I_B = 30$ mAdc) ($I_C = 2.0$ Adc, $I_B = 40$ mAdc)	BD677, 679, 681 BD675A, 677A, 679A	V _{CE(sat)}	- -	2.5 2.8	Vdc
Base–Emitter On Voltage, (Note 1) $ (I_C = 1.5 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}) $ $ (I_C = 2.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}) $	BD677, 679, 681 BD675A, 677A, 679A	V _{BE(on)}	- -	2.5 2.5	Vdc
YNAMIC CHARACTERISTICS					
Small Signal Current Gain (I _C = 1.5 Adc, V _{CF} = 3.0 Vdc, f = 1.0 MHz)		h _{fo}	1.0	_	_

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

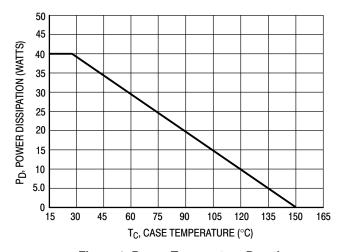


Figure 1. Power Temperature Derating

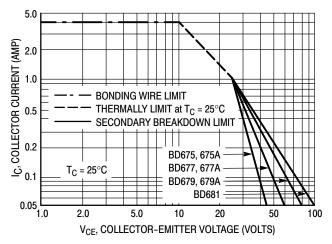


Figure 2. DC Safe Operating Area

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

BD675, BD675A, BD677, BD677A, BD679, BD679A, BD681

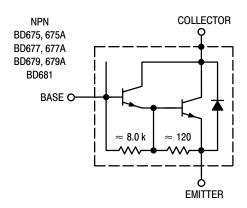


Figure 3. Darlington Circuit Schematic

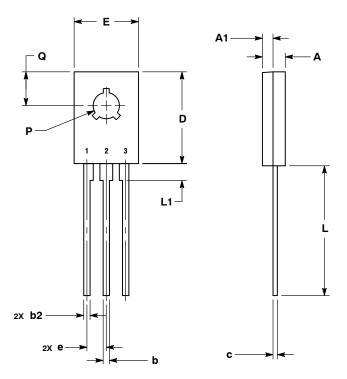
ORDERING INFORMATION

Device	Package	Shipping
BD675G	TO-225AA (Pb-Free)	500 Units / Box
BD675AG	TO-225AA (Pb-Free)	500 Units / Box
BD677G	TO-225AA (Pb-Free)	500 Units / Box
BD677AG	TO-225AA (Pb-Free)	500 Units / Box
BD679G	TO-225AA (Pb-Free)	500 Units / Box
BD679AG	TO-225AA (Pb-Free)	500 Units / Box
BD681G	TO-225AA (Pb-Free)	500 Units / Box

BD675, BD675A, BD677, BD677A, BD679, BD679A, BD681

PACKAGE DIMENSIONS

TO-225 CASE 77-09 **ISSUE AA**



NOTES

- 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.40	3.00	
A1	1.00	1.50	
b	0.60	0.90	
b2	0.51	0.88	
С	0.39	0.63	
D	10.60	11.10	
Е	7.40	7.80	
е	2.04	2.54	
L	14.50	16.63	
L1	1.27	2.54	
Р	2.90	3.30	
Q	3.80	4.20	

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